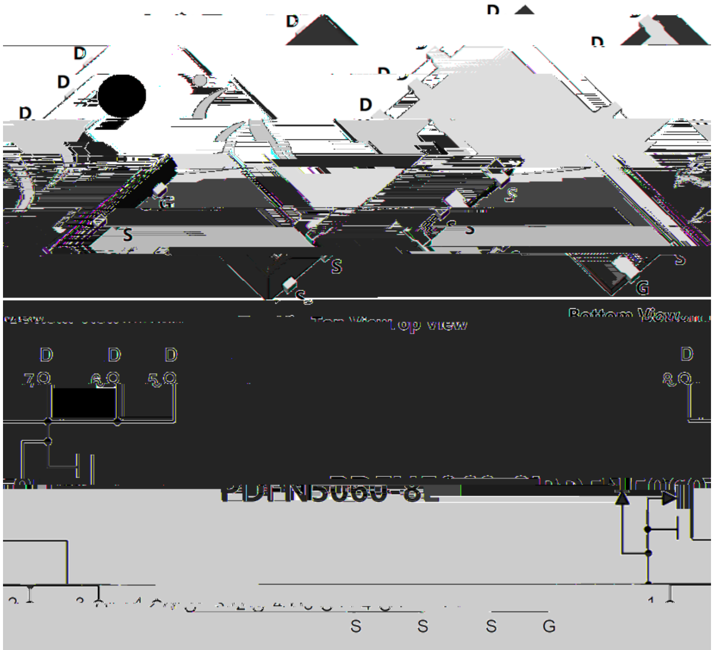
N-Channel Enhancement Mode Field Effect Transistor



Product Summary

● V_{DS}	40V
● I_D	60A
● $R_{DS(ON)}$(at V_{GS}=10V)	Ø6.8mΩ
● 100% EAS Tested	
● 100% j V_A M	

■ Absolute Maximum Ratings (T_A=25 unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	40	V
Gate-source Voltage		V_{GS}	±20	V
Drain Current	T_A=25 -	I_D	12	A
	T_A=100 -		8.4	
	T_C=25 -		60	
	T_C =100 -		42	
Pulsed Drain Current [A]		I_{DM}	240	A
Avalanche energy [B]		EAS	84	mJ
Total Power Dissipation [C]	T_A=25 -	P_D	2.7	W
	T_A=100 -		1.3	
	T_C=25 -		73	

[D]	Steady-State	$R_{θJA}$	46	55	- /W
Thermal Resistance Junction-to-Case	Steady-State	$R_{θJC}$	1.7	2.04	

■ Ordering Information (Example)

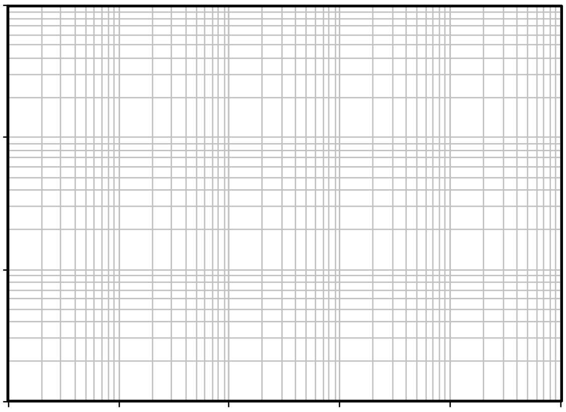
PREFERED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJG60G04HHQ	F1	YJG60G04H	5000	10000	100000	13“ reel

■ **Electrical Characteristics** (T_J=25 unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						

Figure 7. $R_{DS(on)}$ VS Drain Current

Figure 8. Forward characteristic



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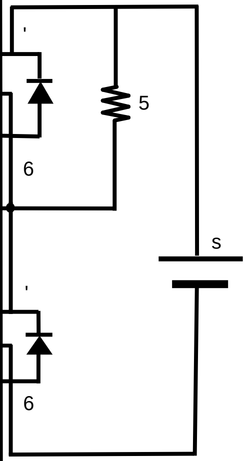
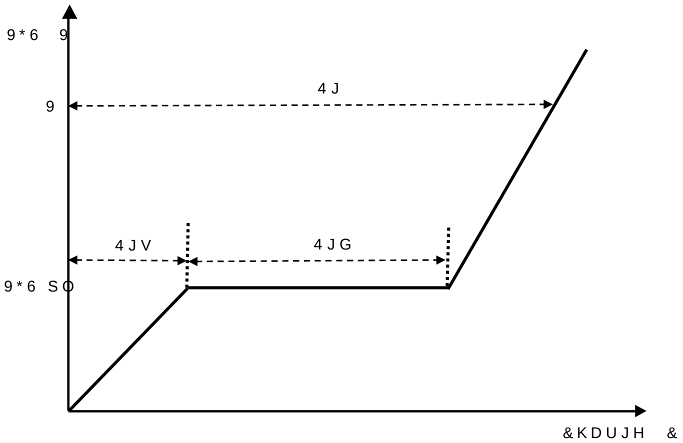
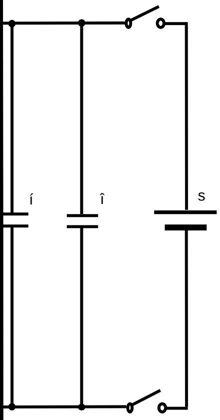




)LJXÙUH D%WH &KDUJHUFHXLVW & :DYHIRUP



■ PDFN5060-8L-1.1MM Packagon "

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p'LVFODLPHU

7KH LQIRUPDWLRQ SUHVHQWHG LQ WK\LV <DQJ]KRX <DQJMLH (OHFWURQLF 7HFKQRORJ\ &R

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